

Silicon NPN Power Transistor

BU326S

DESCRIPTION

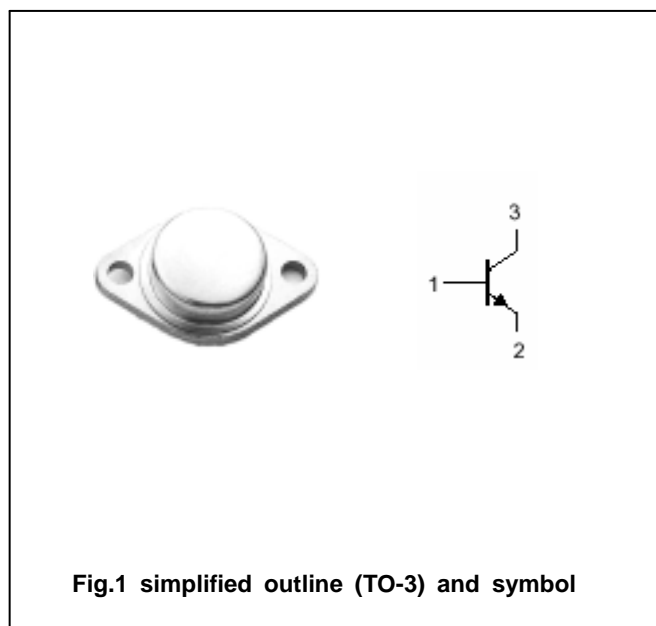
- With TO-3 package
- High voltage;high speed
- Low collector saturation voltage.

APPLICATIONS

- Intended for operating in CTV receiver's chopper supplies.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings (T_c=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	10	V
I _C	Collector current		6	A
I _{CM}	Collector current-peak		8	A
I _B	Base current		3	A
P _T	Total power dissipation	T _c =25	75	W
T _j	Junction temperature		-65~200	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	2.33	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	400			V
V _{CE(sat)-1}	Collector-emitter saturation voltage	I _C =2.5 A; I _B =0.5A			1.5	V
V _{CE(sat)-2}	Collector-emitter saturation voltage	I _C =4A; I _B =1.25 A			3.0	V
V _{BE(sat)-1}	Base-emitter saturation voltage	I _C =2.5 A; I _B =0.5A			1.4	V
V _{BE(sat)-2}	Base-emitter saturation voltage	I _C =4A; I _B =1.25 A			1.6	V
I _{CES}	Collector cut-off current	V _{CE} =800V; V _{BE} =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =10V; I _C =0			10	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V		25		
f _T	Transition frequency	I _C =0.2A ; V _{CE} =10V; f=1MHz	4.0			MHz

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PACKAGE OUTLINE

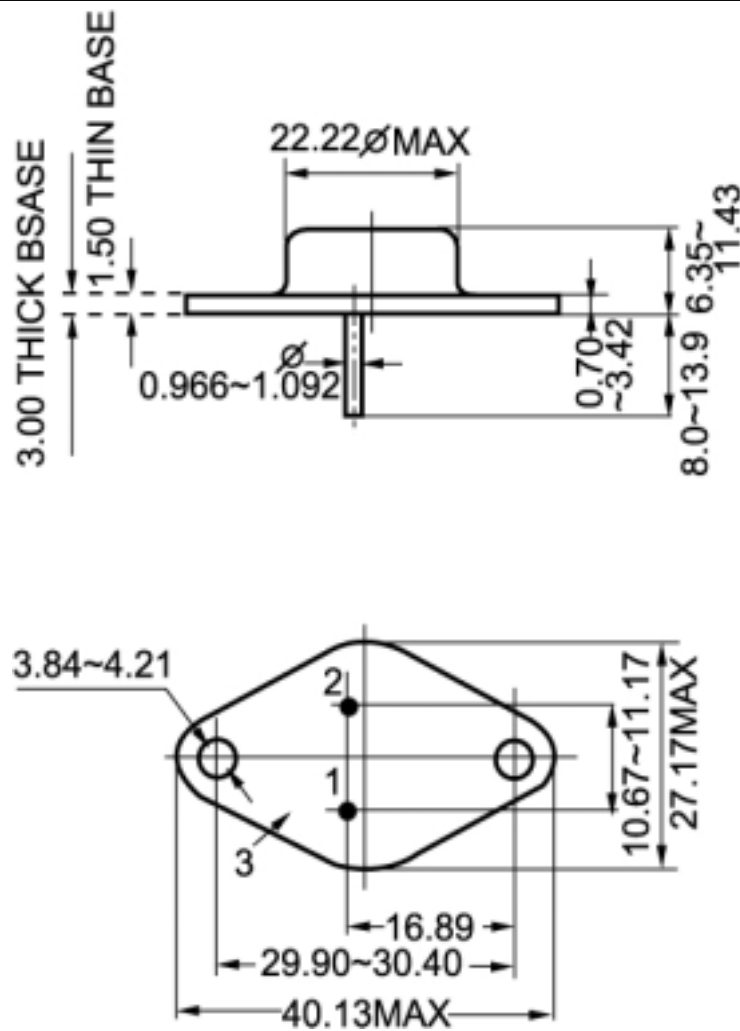


Fig.2 Outline dimensions